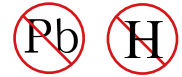
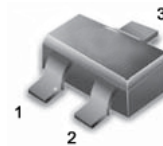


**General Purpose Transistors****PNP Silicon****FEATURE**

We declare that the material of product compliance with RoHS requirements.

**SOT-23 (TO-236AB)****ORDERING INFORMATION**

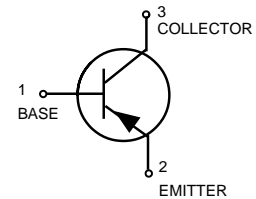
Device	Package	Shipping
9012X	SOT-23	3000/Tape&Reel

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	20	V
Collector-Base Voltage	$V_{CBO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector current-continuoun	$I_C$	500	mA <sub>dc</sub>

**THERMAL CHARATEERISTICS**

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, $T_A=25^{\circ}\text{C}$	$P_D$	225	mW
Derate above $25^{\circ}\text{C}$		1.8	mW/ $^{\circ}\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^{\circ}\text{C/W}$
Total Device Dissipation Alumina Substrate, $T_A=25^{\circ}\text{C}$	$P_D$	300	mW
Derate above $25^{\circ}\text{C}$		2.4	mW/ $^{\circ}\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^{\circ}\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$

**DEVICE MARKING**

9012P=12P	9012Q=12Q
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**ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Characteristic	Symbol	Min	Typ	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage ( $I_C=1.0\text{mA}$ )	$V_{(BR)CEO}$	20	-	-	V
Emitter-Base Breakdown Voltage ( $I_E=100\text{ }\mu\text{A}$ )	$V_{(BR)EBO}$	5	-	-	V
Collector-Base Breakdown Voltage ( $I_C=100\text{ }\mu\text{A}$ )	$V_{(BR)CBO}$	40	-	-	V
Collector Cutoff Current ( $V_{CB}=35\text{V}$ )	$I_{CBO}$	-	-	150	nA
Emitter Cutoff Current ( $V_{BE}=4\text{V}$ )	$I_{EBO}$			150	nA

# PACKAGE OUTLINE & DIMENSIONS

## 9012P/Q

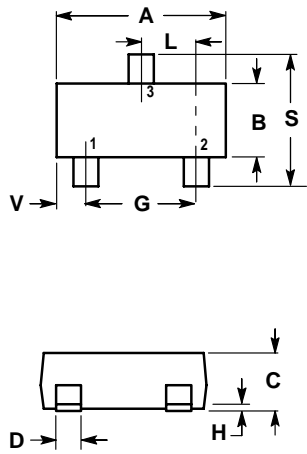
### ON CHARACTERISTICS

DC Current Gain (Ic=50mA, VCE=1V)	Hfe	100	-	300	
Collector-Emitter Saturation Voltage (Ic=500mA, Ib=50mA)	VCE(S)	-	-	0.6	V

NOTE :

*	P	Q
hFE	100~200	150~300

### SOT-23 (TO-236AB)



### NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETERS
- 2. LEAD THICKNESS SPECIFIED PER L / F DRAWING WITH SOLDER PLATING.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR

